

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device, comprising:
  - a first conductive layer formed on a substrate;
  - an insulating interlayer positioned over the first conductive layer, the insulating interlayer having a contact hole, going through the insulating interlayer, that is at least partially disposed directly on the first conductive layer; and
    - a second conductive layer formed on the insulating interlayer, the second conductive layer being electrically coupled to the first conductive layer through the contact hole; the contact hole extending beyond either an edge of the first conductive layer or an edge of the second conductive layer in plan view; and
      - the first conductive layer entirely overlapping the contact hole and the second conductive layer partially overlapping the contact hole in plan view; and
      - one of the first conductive layer and the second conductive layer extending parallel to one another at a predetermined pitch.
- 2-4. (Canceled)
5. (Previously Presented) The semiconductor device according to ~~claim 4~~claim 1, one of the first and second conductive layers intersecting the other of the first and second conductive layers.
6. (Previously Presented) The semiconductor device according to one of claim 1, the second conductive layer overlapping the contact hole that is shifted to one side of the second conductive layer.
7. (Previously Presented) The semiconductor device according to claim 1, the second conductive layer overlapping the contact hole, two opposing edges of the contact hole being outside of the second conductive layer.

8. (Currently Amended) The semiconductor device according to claim 1, the contact hole being rectangular, but not square, in plan view and the second conductive layer partially overlapping the contact hole in a lengthwise direction.

9. (Currently Amended) The semiconductor device according to claim 1, the contact hole being rectangular, but not square, in plan view and the second conductive layer extending diagonally with respect to edges of the contact hole.

10. (Original) An electro-optical unit, the semiconductor device according to claim 1 being used for a substrate of the electro-optical unit to hold an electro-optical substance and pixels having pixel switching transistors, and pixel electrodes being disposed in a matrix on the substrate of the electro-optical unit.

11. (Original) The electro-optical unit according to claim 10, the electro-optical substance being liquid crystal disposed between the substrate of the electro-optical unit and a counter substrate.

12. (Original) The electro-optical unit according to claim 10, the electro-optical substance being an organic electroluminescent substance that constitutes light emitting elements on the substrate of the electro-optical unit.

13. (Original) An electronic apparatus comprising the electro-optical unit according to claim 10.